

Singel 3 | B-2550 Kontich | Belgium | Tel. +32 (0)3 458 30 33 | info@alcom.be | www.alcom.be | www.alcom.be | www.alcom.nl | w

high reliability discrete semiconductor up-screening guide



www.centralsemi.com

A heritage of outstanding quality

Since 1974, Central Semiconductor has manufactured innovative discrete semiconductors for OEM products worldwide. Devices are available in surface mount, through-hole and bare die. Epoxy molded, glass passivated, and hermetically sealed packages are available for a broad range of device types. Central maintains ISO 9001:2015 certification.

Devices include:

- Small signal transistors
- Bipolar power transistors
- MOSFETs/JFETs
- EOS protection devices (TVS)
- Diodes/Rectifiers
- Thyristors
- Multi Discrete Modules (MDM™)

Central Semiconductor has the capability to screen COTS devices to a variety of standards.







Quality by design

Central's designs provide superior performance and reliability with only superior materials used in the construction of its devices. Central's devices meet or exceed commercial performance standards and outperform industry expectations.

In a world where imperfection is all too often accepted, Central constantly monitors its manufacturing processes and business practices to achieve perfect quality products and outstanding service. Continuous improvement opportunities are regularly identified and implemented from within the organization.

High reliability up-screening

Central offers in-house up-screening solutions to ensure the highest quality devices for the most demanding high reliability applications. To best suit the constantly changing requirements of designers, up-screening and complete design solutions are available for both bare die and packaged devices.

Bare die solutions

Central has the capability to perform MIL-PRF-38534 and MIL-PRF-19500 equivalent up-screening, and maintains an extensive wafer inventory in its Long Island, NY facility.

MIL-PRF-38534

Class H and K equivalents

MIL-PRF-19500

Class HC and KC equivalents

Customer-specific up-screening

Customer SCDs are reviewed and all requirements confirmed

Packaged device solutions

Central Semiconductor has standard up-screening solutions which meet the majority of customer requests.



J-lite (JL)

COTS devices up-screened to a streamlined high reliability test flow



JX-lite (JXL)

Lite version of JANTX with a streamlined test flow



EX (EX)

JANTX MIL-PRF-19500 equivalent



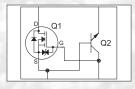
spacellite[™] (SL)

Specialized testing at a lower cost, ideal for low Earth orbit (LEO) applications

Custom solutions

Your vision is our mission. When standard is not enough, Central excels at listening to customers' challenges and designing custom solutions that other manufacturers have no interest in pursuing. **Just ask.**





Options include:

- Electrical parameter screening
- Custom wafer diffusion and metallization
- Standard/customer-specific testing and up-screening



Super Industrial[™] enhanced solutions include:

- Customer-specific high reliability testing
- Custom interconnect
- Custom packaging

Testing capabilities

All tests performed to MIL-STD-750 or MIL-STD-883 (bare die) test methods. Central provides dependable management of work flow with accurate device identification throughout the process.



Thermal stream testing



Temperature cycle testing



Particle Impact Noise Detection (PIND)



Burn-in testing



High temperature & humidity testing



Fine leak testing



Gasket fabrication for package decapsulation



X-Ray analysis



Digital microscope analysis



Scanning Electron Microscopy (SEM)



Highly-accelerated stress testing (HAST)



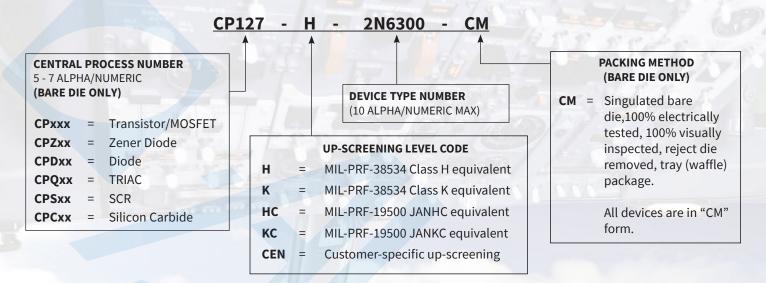
Wire pull & die shear testing

Part number nomenclature

The following is a guide to Central's up-screened and custom device part numbers.

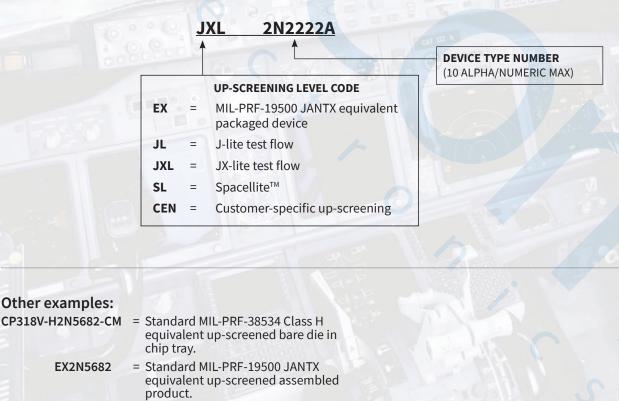
Bare die devices - (example: CP127-H2N6300-CM)

Bipolar transistor die, up-screened to MIL-PRF-38534 Class H equivalent, 2N6300 device, packaged in chip tray.



Packaged devices - (example: JXL2N2222A)

JX-lite certified version of a Central Semiconductor 2N2222A transistor.



CEN1234 = Custom device up-screened to MIL-PRF-19500 equivalent or customer-defined test specifications. (1234 represents a custom item)

Test Flow: Class H equivalent die

| MIL-PRF-38534 Class H Equivalent Up-Scree | ening | |
|---|---|--|
| Screening Requirements | As | |
| Test | Quantity (Accept Number of Failures) | Specification and Test Method |
| Subgroup 1: Electrical Test | 100% | |
| Subgroup 2: Visual Inspection | 100% | MIL-STD-750: 2069, 2070, 2072, 2073 |
| Subgroup 3A: Internal/Die Visual Inspection | 10 (0) | MIL-STD-750: 2069, 2070, 2072, 2073 |
| Subgroup 3B: Sample Assembly | 10 (0) | |
| Subgroup 4: Electrical Test as per Data- sheet: DC Test @ 25°C / DC Test @ 125°C / DC Test @-55°C/ (DC1-DC3) | 10 (0) | |
| Subgroup 5 Wire Pull | 10 Wires (0) or 20 Wires (1) | MIL-STD-883: 2011 Cond. D |

CCS983 (R0)

Test Flow: Class K equivalent die

| MIL-PRF-38534 Class K Equivalent Up-scree | ning | |
|---|---|---|
| Screening Requirements | | |
| Test | Quantity (Accept Number of Failures) | Specification and Test Method |
| Subgroup 1: Electrical Test | 100% | |
| Subgroup 2: Visual Inspection | 100% | MIL-STD-883: 2010 |
| | | MIL-STD-750: 2069, 2070, 2072, 2073 |
| Subgroup 3A: Internal/Die Visual Inspection | 10 (0) | MIL-STD-883: 2010 |
| | | MIL-STD-750: 2069, 2070, 2072, 2073 |
| Subgroup 3B: Sample Assembly | 10 | |
| Subgroup 4A: Electrical Test as per Data- sheet: DC Test @25°C (DC1) | 10 devices per wafer (0) | |
| Subgroup 4B: Temperature Cycling | 10 devices per wafer (0) | MIL-STD-883:1010-C 10 Cycles Minimum |
| Subgroup 4C: Mechanical Shock or Constant Acceleration | 10 devices per wafer (0) | MIL-STD-750: 2002 or 2001 B, Y1 direction or 3000 g's Y1 Direction |
| Subgroup 4D: Electrical Test as per Data- sheet: DC Test @ 25°C / DC Test @ 125°C /DC Test @-55°C/ (DC2-DC4) | 10 devices per wafer (0) | |
| Subgroup 4E: HTRB | 10 devices per wafer (0) | MIL-STD-883: 1015-A 240 Hours, TA Minimum 125°C |
| Subgroup 4F: Electrical Test as per Data- sheet: DC Test @ 25°C / DC Test @ 125°C / DC Test @-55°C/ (DC5-DC7) | 10 devices per wafer (0) | |
| Subgroup 4G: Steady State Life | 10 devices per wafer (0) | MIL-STD-883: 1005-B 1000 Hours, TC Minimum 125°C |
| Subgroup 4H: Electrical Test as per Data- sheet: DC Test @ 25°C / DC Test @ 125°C / DC Test @-55°C/ (DC8-DC10) | 10 devices per wafer (0) | |
| Subgroup 5: Wire Pull | 10 Wires (0) or 20 Wires (1) | MIL-STD-883: 2011-D |
| Subgroup 6: SEM | Per Mil Standard | MIL-STD-750: 2077 |

CCS986 (R0)

Test Flow: Class HC equivalent die

| MIL-PRF-19500 JANHC Equivalent Up-Scree | ning | |
|---|--|--------------------------------------|
| Screening Requirements | Mala | d de s |
| Test | Quantity (Accept Number of Failures) | MIL-STD-750 |
| Subgroup 1: Electrical Test (DC1) | 100% | |
| Subgroup 2: Visual Inspection | 100% | 206 <mark>9,</mark> 2070, 2072, 2073 |
| Subgroup 3A: Internal/Die Visual Inspection | 10 (0) | 2069, 2070, 2072, 2073 |
| Subgroup 3B: Sample Assembly | 10 | |
| Subgroup 4A: Temperature Cycling | 10 (0) | 1051-C |
| Subgroup 4B: Electrical Test as per Data- sheet: DC Test @ 25°C / DC Test @ -55°C / DC Test @150°C / AC Test @ 25°C (DC2-DC4), (AC1) | 10 (0) | As per Electrical Datasheet |
| Subgroup 4C: HTRB | 10 (0) | 1039-А, 1042-В, 1038-А |
| Subgroup 4D: Electrical Test (DC5) | 10 (0) | As per Electrical Datasheet |
| Subgroup 4E: Burn-In/SSOP | 10 (0) | 1039-В, 1042-А, 1038-В |
| Subgroup 4F: Electrical Test as per Data- sheet: DC Test @ 25°C (DC6) | 10 (0) | As per Electrical Datasheet |
| Subgroup 5A: Wire Pull | 10 Wires (0) or 20 Wires (1) | 2037 |
| Subgroup 5B: Die Shear | 5(0) or 10 (1) | 2017 |

CCS984 (R0)

Test Flow: Class KC equivalent die

| Screening Requirements | | |
|--|---|--|
| Test | Quantity (Accept Number of Failures) | MIL-STD-750 |
| Subgroup 1: Electrical Test | 100% | |
| Subgroup 2: Visual Inspection | 100% | TM: 2069, 2070, 2072, 2073 |
| Subgroup 3A: Internal/Die Visual Inspection | 22 devices per wafer (0) | TM: 2069, 2070, 2072, 2073 |
| Subgroup 3B: Sample Assembly | 22 devices per wafer (0) | |
| Subgroup 4A: Temperature Cycling | 22 devices per wafer (0) | TM: 1051-C |
| Subgroup 4B: Mechanical Shock or Constant | 22 devices per wafer (0) | TM: 2016 or 2006 |
| Acceleration | | Y1 Axis Direction |
| Subgroup 4C: Electrical Test: DC Test @ 25°C / DC Test @ TA MIN / DC Test @ TA MAX/ AC Test @ 25°C (DC2-DC4) (AC1) AC Test are performed when applicable | 22 devices per wafer (0) | As per Electrical Datasheet |
| Subgroup 4D: HTRB | 22 devices per wafer (0) | ТМ:1038-А, 1039-А, 1042-В |
| Subgroup 4E: Electrical Test (DC5) | 22 devices per wafer (0) | As per Electrical Datasheet |
| Subgroup 4F: Burn-In | 22 devices per wafer (0) | ТМ:1038-В, 1039-В, 1040-А,1042-А |
| Subgroup 4G: Electrical Test: DC Test @ 25°C (DC6) | 22 devices per wafer (0) | As per Electrical Datasheet |
| Subgroup 4H: Steady State Life | 22 devices per wafer (0) | TM:1038-A or B, 1039-B, 1040-A, 1042-A |
| Subgroup 4I: Electrical Test: DC Test @ 25°C / DC Test @ TA MIN / DC Test @ TA MAX / AC Test @ 25°C (DC7- DC9) | 22 devices per wafer (0) | As per Electrical Datasheet |
| Subgroup 5A: Wire Pull | 10 Wires (0) or 20 Wires (1) | TM:2037 |
| Subgroup 5B: Die Shear | 5(0) or 10 (1) | TM:2017 |
| Subgroup 6: SEM | Per Mil Standard | TM:2077 |
| Subgroup 7A: RHA Total Dose | As per customer requirement | TM: 1019 |
| Subgroup 7B: Neutron Irradiation | As per customer requirement | TM: 1017 |

CCS985 (R0)

Test Flow: J-lite and JX-lite

| J-lite and JX-lite Certific | ation | | | |
|--|----------------|---------------------|--|--|
| Test | Sample Size | Standard | J-lite (JL) | JX-lite (JXL) |
| Serialization | | | Read and Record | Read and Record |
| Number 1: Electrical Test | 100% | | 25°C (DC1) Per Device Datasheet | 25°C, -55°C, 125°C (DC1, DC2, DC3) Per Device Datasheet |
| Number 2: | 100% | MIL-STD-750: | 10 Cycles | 20 Cycles |
| Temperature Cycling | | TM 1051 Condition B | (-55°C to +125°C) | (-55°C to +125°C) |
| Number 3: Electrical Test | 100% | | 25°C (DC2) Per Device Datasheet | 25°C (DC4) Per Device Datasheet |
| Number 4: PIND | 100% | MIL-STD-750: | - | Applicable |
| Hermetic Devices Only | | 2052 Condition A | | |
| Number 5: | 100% | MIL-STD 750: | 48 Hours for Diodes. | 96 Hours for Diodes. |
| HTRB | | 1038-A, 1039-A, | 48 Hours for NPN Transistors. 24 Hours for PNP Transistors. | 96 Hours for NPN Transistors. 48 Hours for PNP Transistors. |
| | | 1040-A, 1042-B | 48 Hours for MOSFETs. | 96 Hours for MOSFETs. |
| Number 6A: | 100% | | 25°C | 25°C |
| Electrical Test | | | (DC3) | (DC5) |
| | | | Per Device Datasheet | Per Device Datasheet |
| Number 6B: Delta Shift Calculations | 100% | | | Per Specified Parameters on Device Datasheet |
| Number 6C: PDA Evaluation | 100% | | | 20% Allowable per Min/Max Limits of Device Datasheet |
| Number 7: Gross Leak | 100% | MIL-STD 750 | Performed | Performed |
| Hermetic Devices Only | | 1071 | | |
| Number 8: Final Electrical Test | 100% | | 25°C (DC4) Per Device Datasheet | 25°C, -55°C, 125°C (DC6, DC7, DC8) Per Device Datasheet |

CCS964 (R1)

Continued on next page

Test Flow: J-lite and JX-lite

| J-lite and JX-lite Qualification | | | | |
|---|-----------------------------|----------------------|------------------|--|
| Process | Test Method & Conditions | Failures/Sample Size | | |
| | | J-lite (JL) | JX-lite (JXL) | |
| MIL-PRF 19500 Gro | oup A | | -2 5 3 | |
| Subgroup 1: Visual and Mechanical Examination | MIL-STD 750: 2071 | 0/45 🧭 | 0/45 | |
| Subgroup 2: DC Testing @ 25°C | | 0/116 | 0/116 | |
| Subgroup 3: DC Testing at High and Low Specified Temperatures | 1357 | 0/116 | 0/116 | |
| Subgroup 4: AC Testing @ 25°C | To LAVY | 0/116 | 0/116 | |
| Subgroup 5: Safe Operation Area (Transistors Only) | As Per Datasheet | 0/45 | 0/45 | |
| Subgroup 6: Surge Current (Diodes/Rectifiers Only) | | 0/22 | 0/22 | |
| Subgroup 7: Selected Static and Dynamic Tests | | 0/22 | 0/22 | |

CCS964 (R1)

Note: 1.

Devices supplied will be to the test flow illustrated above. Any changes to the flow must be agreed upon in writing by the customer and Central Semiconductor Corp. Above are the standard Certification and Qualification test flows for all devices starting with JL (for J-lite) and JXL (for JX-lite) devices.

Example: JL2N2222A

2.

JXL2N2222A

J-lite certified version of a Central Semiconductor 2N2222A
 JX-lite certified version of a Central Semiconductor 2N2222A

Test Flow: EX (JANTX equivalent)

| Certification | | 100% Testing |
|---|----------------|-----------------------|
| MIL-PRF-19500P Appendix E Table E-IV - Screening Requirements | | |
| Test | Sample Size | MIL-STD-750 Method |
| 1a) Die visual For Glass Diodes 1b) Internal visual | | A A |
| 2) High Temperature Life Nonoperating Life | Optional | 1032 |
| 3a) Temperature Cycling | 100% | 1051 |
| 3b) Surge (as specified) | | 17 |
| 3c) Thermal Impedance (as specified) | 100% | 1 Martin |
| 4) Constant Acceleration | | |
| 5) PIND | | |
| 6) Instability Shock Test | | |
| 7) Hermetic Seal F&G | | |
| 8) Serialization | 100% | |
| 9) Interim Electrical Parameters | 100% | |
| 10) HTRB 24 Hours | 100% | 1039 Condition A |
| 11) Interim Electrical Parameters As Specified For Device Type | 100% | |
| 12) Burn-in 160 Hours | 100% | 1039 Condition B |
| 13) Final Electrical Parameters As Specified For Device Type | 100% | |
| 14) Hermetic Seal F&G | 100% | 1071 |
| 15) Radiography | X | |
| 16) External Visual Examination | | DENY NY XO |
| 17) Case Isolation | | |

CCS988 (R1)

Continued on next page

Test Flow: EX (JANTX equivalent)

| EX Qualification | | |
|--|---|--|
| Qualification SubGroups A, B, C, E | | |
| Group A | Group B | |
| Subgroup 1 Visual & Inspection MIL-STD-750 Method 2071 | Subgroup 1 Solderability Resistance To Solvents | |
| Subgroup 2 DC (Static) test @ +25C | Salt Atmosphere Subgroup 2 | |
| Subgroup 3 DC (Static) test @ -65C and +150C | Thermal Shock Glass Diodes Only Temperature Cycling 25 Cyc (20 @ Screening, totaling 45) Surge Current | |
| Subgroup 4 Dynamic test @ +25C | Hermetic Seal Electrical Measurements Per Group A SubG 2 | |
| Subgroup 5 Safe Operating Area Test | Subgroup 3 Steady State Operation Life Biased, 340 Hours Electrical Measurements Per Group A SubG 2 | |
| Subgroup 6 | Hermetic Seal Method 1071 Bond Strength Condition D 11 Wires | |
| Surge Current | Subgroup 4 Decap - Internal Visual; Examination | |
| Subgroup 7 | Subgroup 5 Thermal Resistance Not Applicable - Case Mount Device | |
| Select Static & Dynamic Tests | Subgroup 6 High Temperature Life, Non-Operating 340 Hours Electrical Measurements Per Group A SubG 2 | |

CCS988 (R1)

Continued on next page

Test Flow: EX (JANTX equivalent)

| Group C | Group E | |
|---|--|--|
| Subgroup 1 | Subgroup 1 | |
| Physical Dimensions | Temperature Cycling Hermetic Seal | |
| Subgroup 2 | Electrical Measurements Per Group A SubGroup 2 | |
| Thermal Shock (Glass Diodes Only) | | |
| Temperature Cycling | | |
| Terminal Strength | Subgroup 2 | |
| Hermetic Seal | SS Operation Life Biased, 1000 Hrs | |
| Moisture Resistance | | |
| Electrical Measurements (Per Group A Sub- Group 2) | Subgroup 3 | |
| Subgroup 3 | | |
| Shock Test | Subgroup 4 | |
| Vibration, Variable Frequency | Thermal Impedance Curves | |
| Constant Acceleration | Subgroup 5 | |
| Electrical Measurements (Per Group A Sub- Group 2) | Barometric Pressure | |
| Subgroup 4 | Subgroup 6 | |
| Salt Atmosphere | ESD | |
| Subgroup 5 | | |
| Thermal Resistance | Subgroup 7 | |
| Subgroup 6 | Resistance To Solder Heat | |
| SS Operation Life | Hermetic Seal | |
| Electrical Measurements (Per Group A Sub- Group 2) | Electrical Measurements (Per Group A SubGroup 2) | |
| Hermetic Seal | Subgroup 8 | |
| Bond Strength | Reverse Stability Method 1033 Condition B | |
| Subgroup 7 | | |
| IGA | Subgroup 9 | |
| | Resistance To Glass Cracking | |

CCS988 (R1)

spacellite[™] solutions

what is spacellite[™]

Spacellite discrete semiconductors are devices designed to meet the reliability and functionality specifications for today's modern satellite applications.

why spacellite[™]

- Reduced cost without compromising quality or reliability
- Meets Space 2.0 methodology and directives
- Ideal for low Earth orbit (LEO) applications for the latest satellite technologies
- Equivalent to MIL-PRF-19500 and MIL-PRF-38534 devices



spacellite[™] benefits

- Optional gold wire bonds
- "State of the art" advanced device technology
- Both plastic and hermetic packages available





plastic TO-220 package

hermetic TO-3 package



When standard commercial devices do not meet your requirements, Central Semiconductor's Spacellite[™] devices are the perfect solution.

View Central's spacellite[™] brochure for additional information.

